AMENDMENTS TO THE SPECIFICATION

Please amend the specification of the present application as set forth below. In accordance with the PTO's revised amendment format, changes are shown by strikethrough (for deleted matter) or underlining (for added matter).

In the title, please replace the title with the following title:

METHOD FOR MAKING A SEMICONDUCTOR DEVICE WITH DEPOSITED OXIDE

Please replace paragraph [0028] with the following amended paragraph:

[0028] A pre-diffusion clean step is performed and a polysilicon layer 40 is formed upon patterned, deposited oxide layer 36 as seen in Figure 3. In Figure 4, polysilicon layer 40 is patterned to expose semiconductor substrate 34 through gate oxide 33 where active regions 37, 38 are formed. Active regions 37, 38 can be formed by implanting an N+dopant into semiconductor substrate 34 which may have a p-type doping. The patterning of polysilicon layer 40 results in the formation of a gate oxide 33 associated with an electrode 842. The threshold voltage for gate electrode 42 increases away from active regions 37, 38 underneath each patterned, deposited oxide layers 36. As such, patterned, deposited oxide layers 36 have the same electrical effect as a pair of field oxide regions but without the detrimental problem of dopant depletion inherent to field oxide growth.